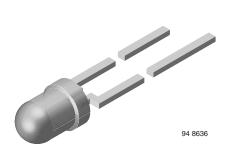
TSHF4410



Vishay Semiconductors

High Speed Infrared Emitting Diode, 890 nm, **GaAlAs Double Hetero**



DESCRIPTION

TSHF4410 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm): Ø 3
- Peak wavelength: λ_p = 890 nm
- High reliability
- High radiant power
- · High radiant intensity
- Angle of half intensity: $\varphi = \pm 22^{\circ}$
- · Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: f_c = 12 MHz
- Good spectral matching with Si photodetectors
- · Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Note

Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

APPLICATIONS

- · Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- · Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)
- Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	l _e (mW/sr)	φ (deg)	λ _p (nm)	tr (ns)	
TSHF4410	40	± 22	890	30	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHF4410	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	5	V
Forward current		١ _F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA
Surge forward current	t _p = 100 μs	I _{FSM}	1.5	A

Document Number: 81276



<u>GREEN</u> (5-2008)

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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Power dissipation		P _V	180	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	300	K/W	

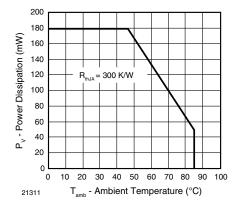


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

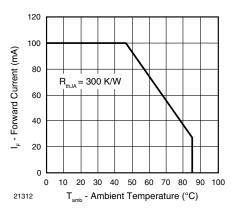


Fig. 1 - Forward Current Limit vs. Ambient Temperature

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward valtage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.5	1.8	V
Forward voltage	I _F = 1 A, t _p = 100 μs	V _F		2.4	3.0	V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	Cj		125		pF
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e		40		mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	l _e		400		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе		40		mW
Temperature coefficient of ϕ_{e}	l _F = 100 mA	TKφ _e		- 0.35		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	l _F = 100 mA	λρ		890		nm
Spectral bandwidth	l _F = 100 mA	Δλ		44		nm
Temperature coefficient of λ_p	l _F = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	l _F = 100 mA	t _r		30		ns
Fall time	I _F = 100 mA	t _f		30		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c		12		MHz
Virtual source diameter	Method: 63 % encircled energy	d		1.9		mm



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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

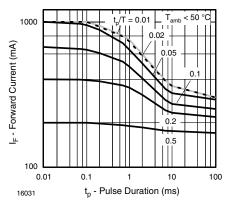


Fig. 2 - Pulse Forward Current vs. Pulse Duration

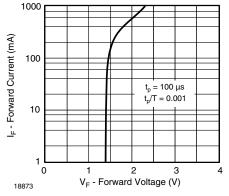


Fig. 3 - Forward Current vs. Forward Voltage

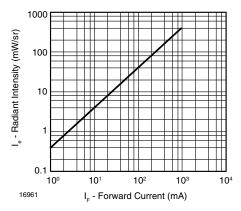


Fig. 4 - Radiant Intensity vs. Forward Current

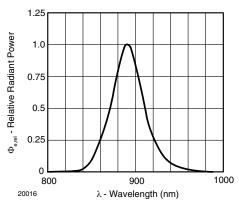


Fig. 5 - Relative Radiant Power vs. Wavelength

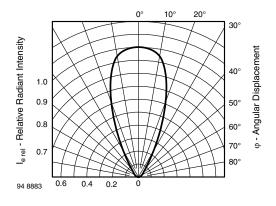


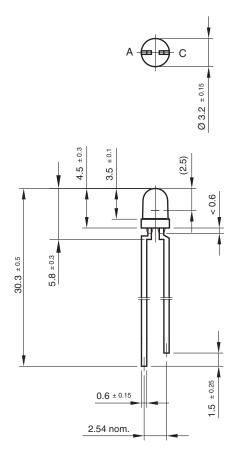
Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

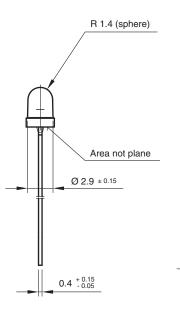
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PACKAGE DIMENSIONS in millimeters







technical drawings according to DIN specifications

Drawing-No.: 6.544-5255.01-4 Issue: 7; 25.09.08 95 10913



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